

A High-power-density WR-3.4 Power Amplifier in 250-nm InP DHBT Technology

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Introduction

Advantages of the sub-THz spectrum:

- Wide frequency range for the application of ultra-high-speed wireless communication systems
- Suitable for various applications such as radar, imaging systems, and optical signal processing

High-Power Density Power Amplifier (PA) Requirements:

- Compact chip area with high output power for phased array systems
- Low-loss and wideband power combining structures for enhanced output power

Design

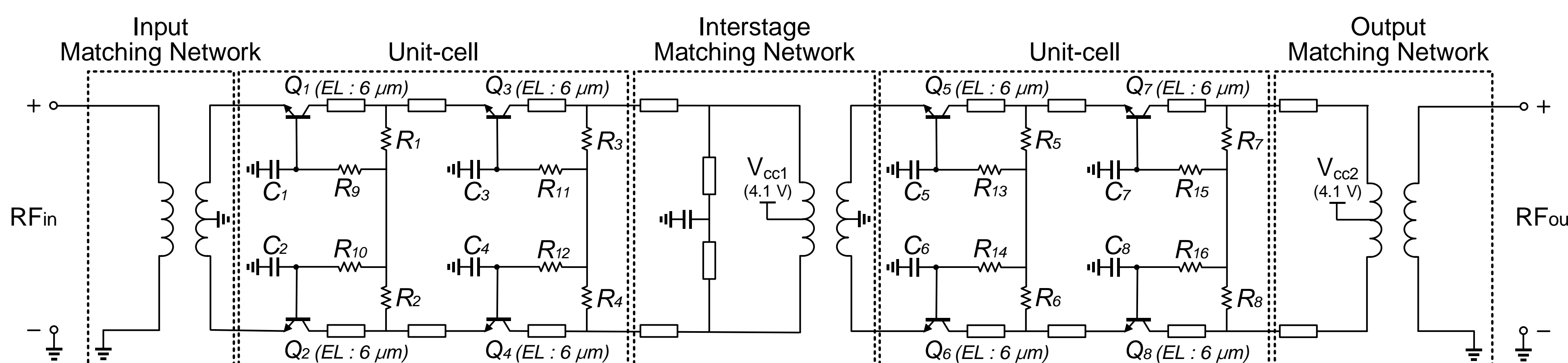
1-chain common-base (CB) PA

- High-power differential double-stacked CB unit-cell
- Emitter length selection based on DC power consumption and impedance transformation ratio
- Impedance matching based on transformer network, transmission lines, and stubs

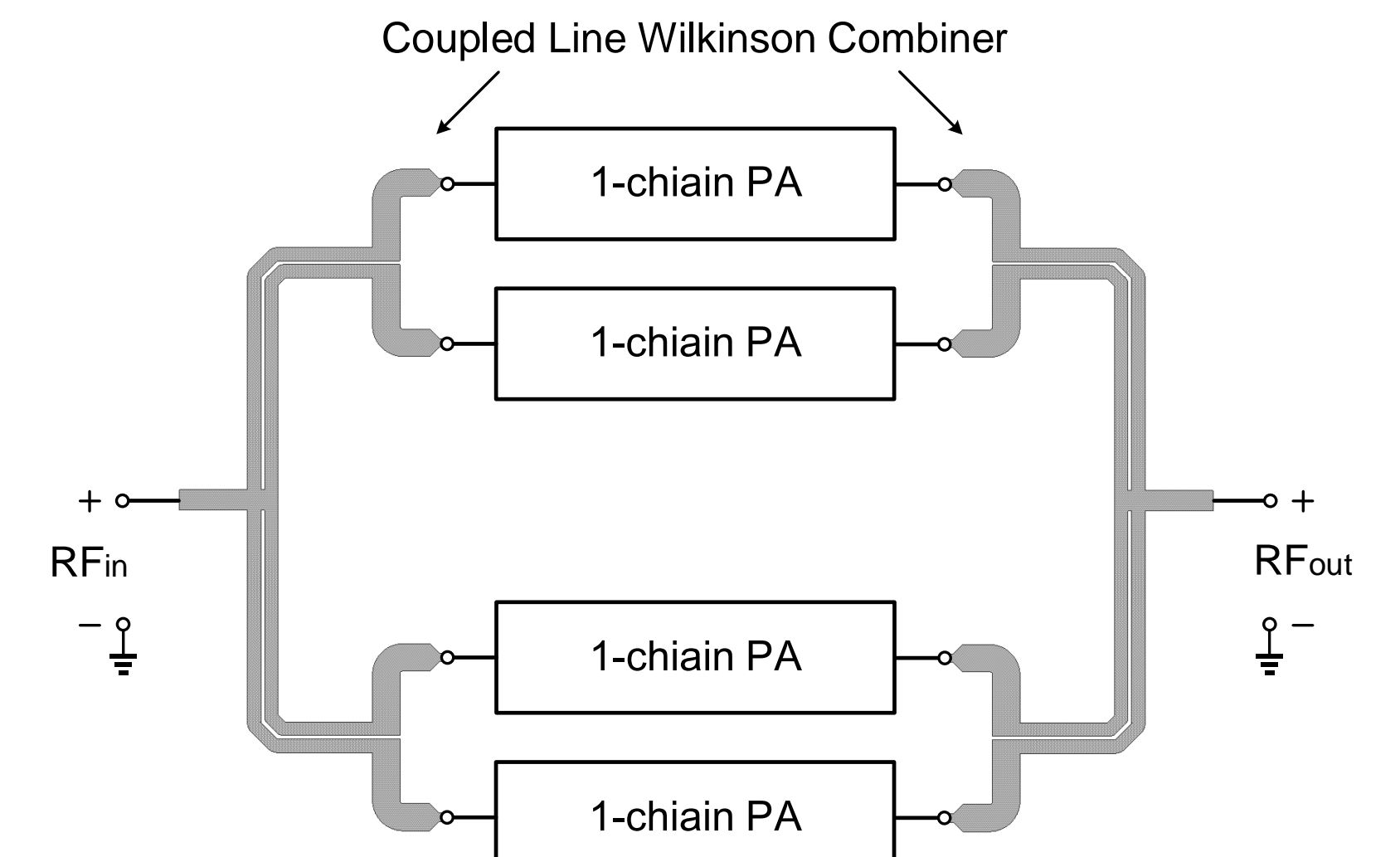
High output power 4-chain CB PA

- Four 1-chain CB PAs combined using a coupled-line Wilkinson combiner
- Using the odd and even-mode characteristic impedances of coupled-line for impedance matching
- Enhanced output power with efficient combining

(Schematic of the 1-chain CB PA)



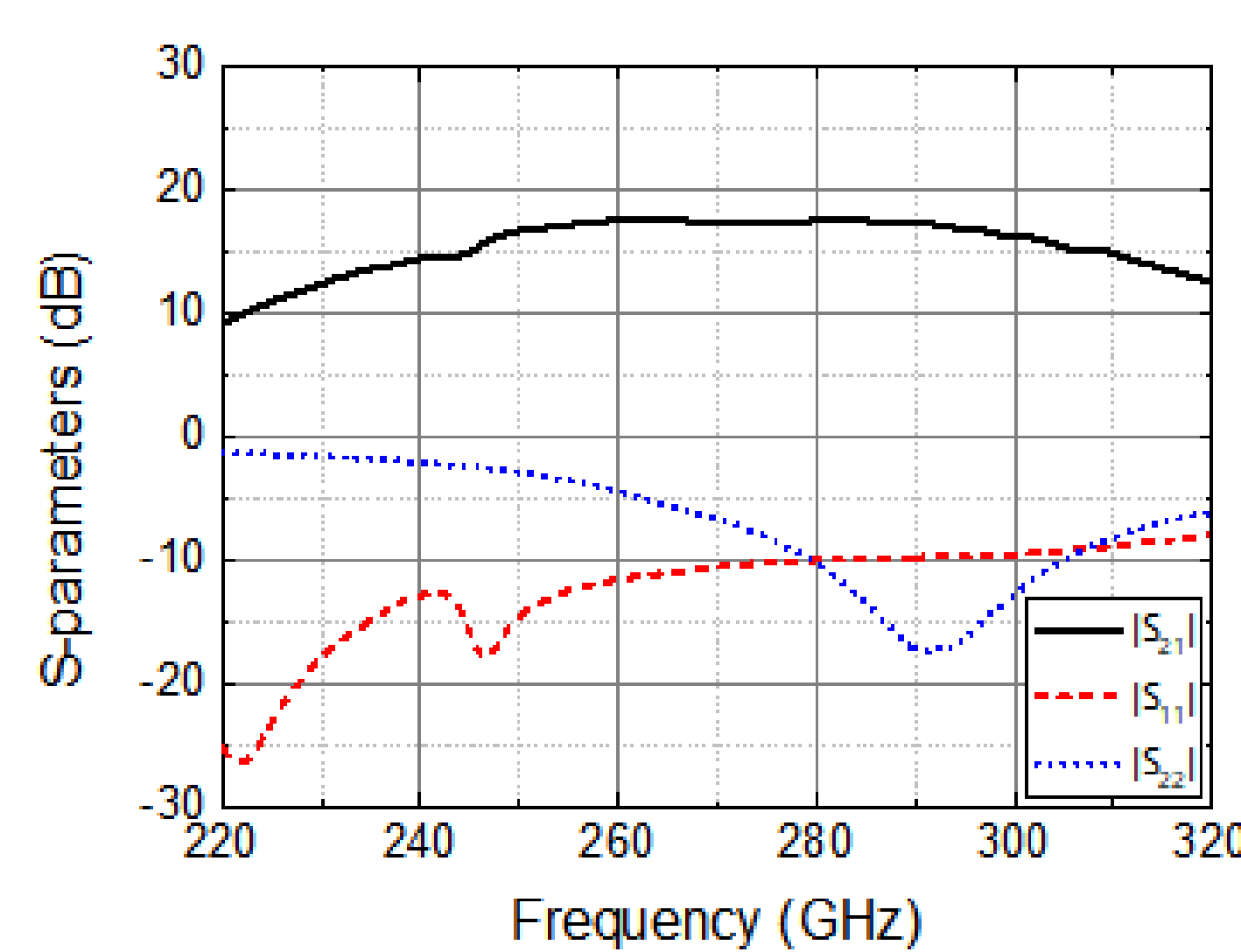
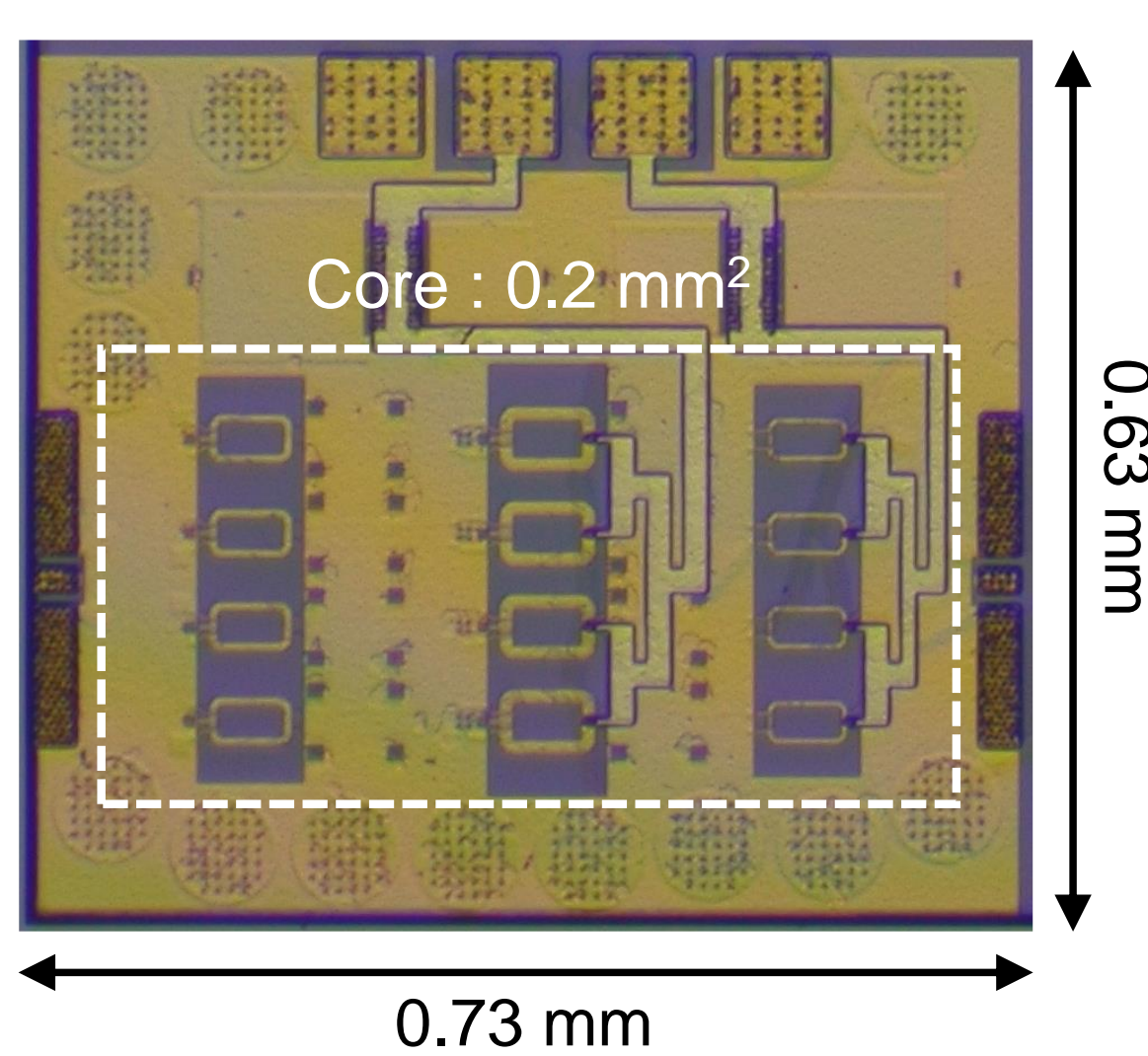
(Diagram of the 4-chain CB PA)



Results

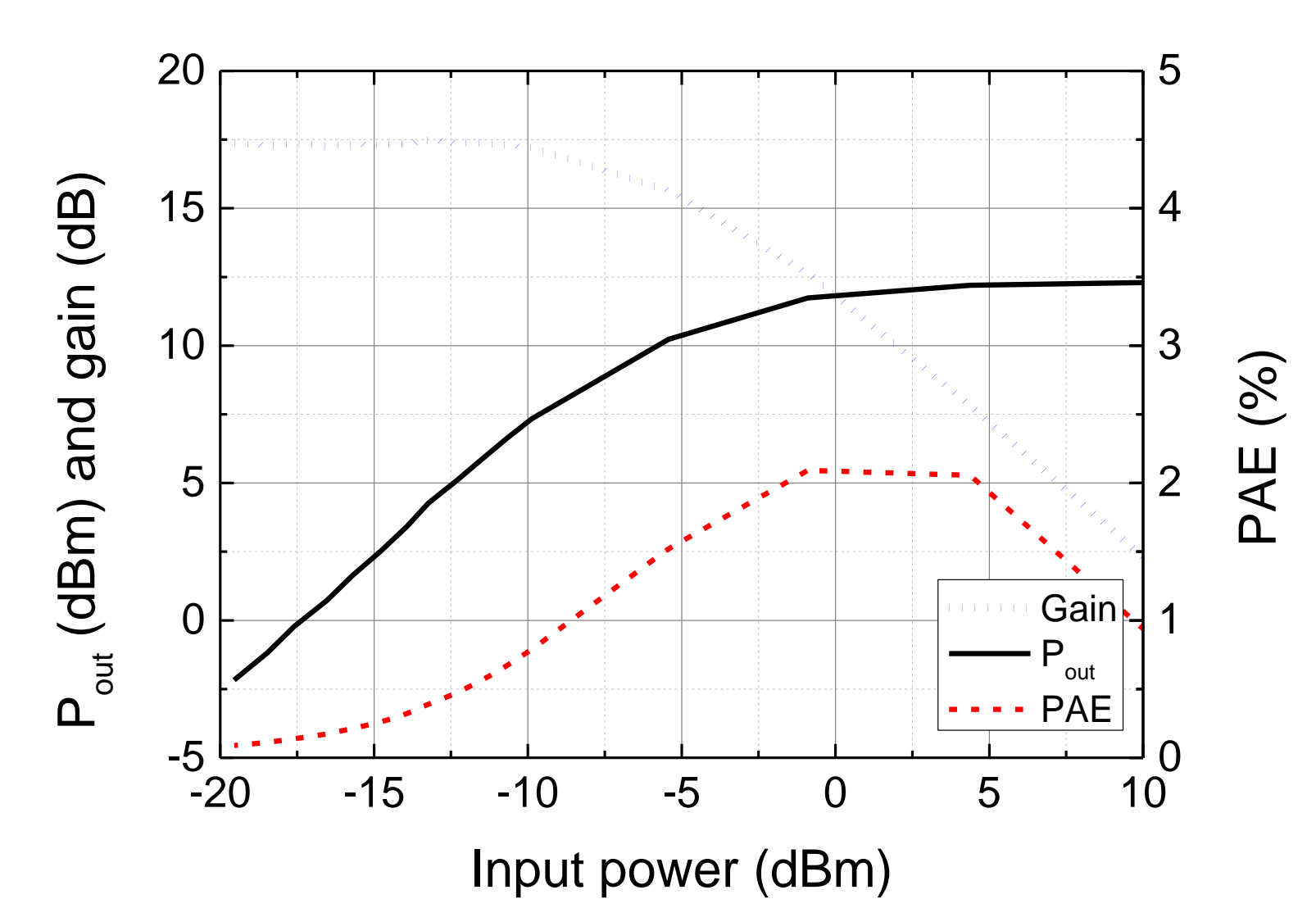
Chip photograph & simulated S-parameters

- Chip size = $0.73 \times 0.63 \text{ mm}^2$ (Core size = 0.2 mm^2)
- Peak $|S_{21}|$ = 17.5 dB @ 282 GHz
- 3-dB BW = 69 GHz (243–312 GHz)



Measured power performances @ 270 GHz

- P_{sat} = 12.4 dBm
- Peak PAE = 2.0 %
- Power density = 86.9 mW/mm²



Conclusion

- Design of a high-power-density WR-3.4 power amplifier using 250-nm InP DHBT process
- 4-way coupled-line Wilkinson combiner structure utilized for matching, resulting in a compact chip size
- Achieved P_{sat} of 12.4 dBm with a power density of 86.9 mW/mm²

The chip fabrication and EDA tool were supported by the IC Design Education Center(IDEC), Korea